HM6208H Series

65,536-word × 4-bit High Speed CMOS Static RAM

HITACHI

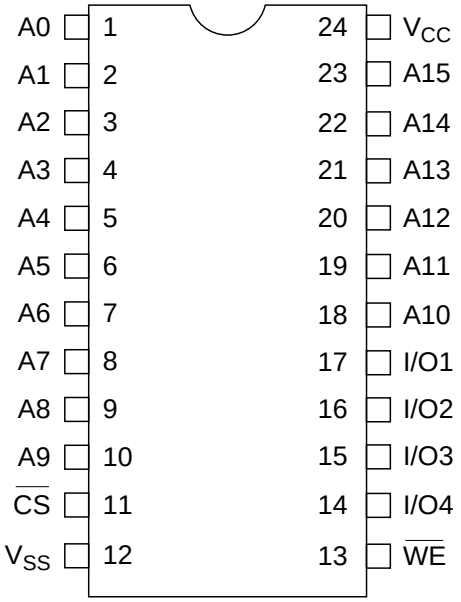
Features

- Single 5 V supply and high density 24-pin package
- High speed: Access time 25/35/45 ns (max)
- Low power
  - — Operation: 300 mW (typ)
  - — Standby: 100 µW (typ)
    30 µW (typ) (L-version)
- Completely static memory required
  - — No clock or timing strobe required
- Equal access and cycle time
- Directly TTL compatible: All inputs and outputs
- Battery backup operation capability (L-version)

Ordering Information

Type No.	Access Time	Package
HM6208HP-25	25 ns	300-mil, 24-pin plastic DIP (DP-24NC)
HM6208HP-35	35 ns	
HM6208HP-45	45 ns	
HM6208HLP-25	25 ns	
HM6208HLP-35	35 ns	
HM6208HLP-45	45 ns	
HM6208HJP-25	25 ns	300-mil, 24-pin SOJ (CP-24D)
HM6208HJP-35	35 ns	
HM6208HJP-45	45 ns	
HM6208HLJP-25	25 ns	
HM6208HLJP-35	35 ns	
HM6208HLJP-45	45 ns	

Pin Arrangement

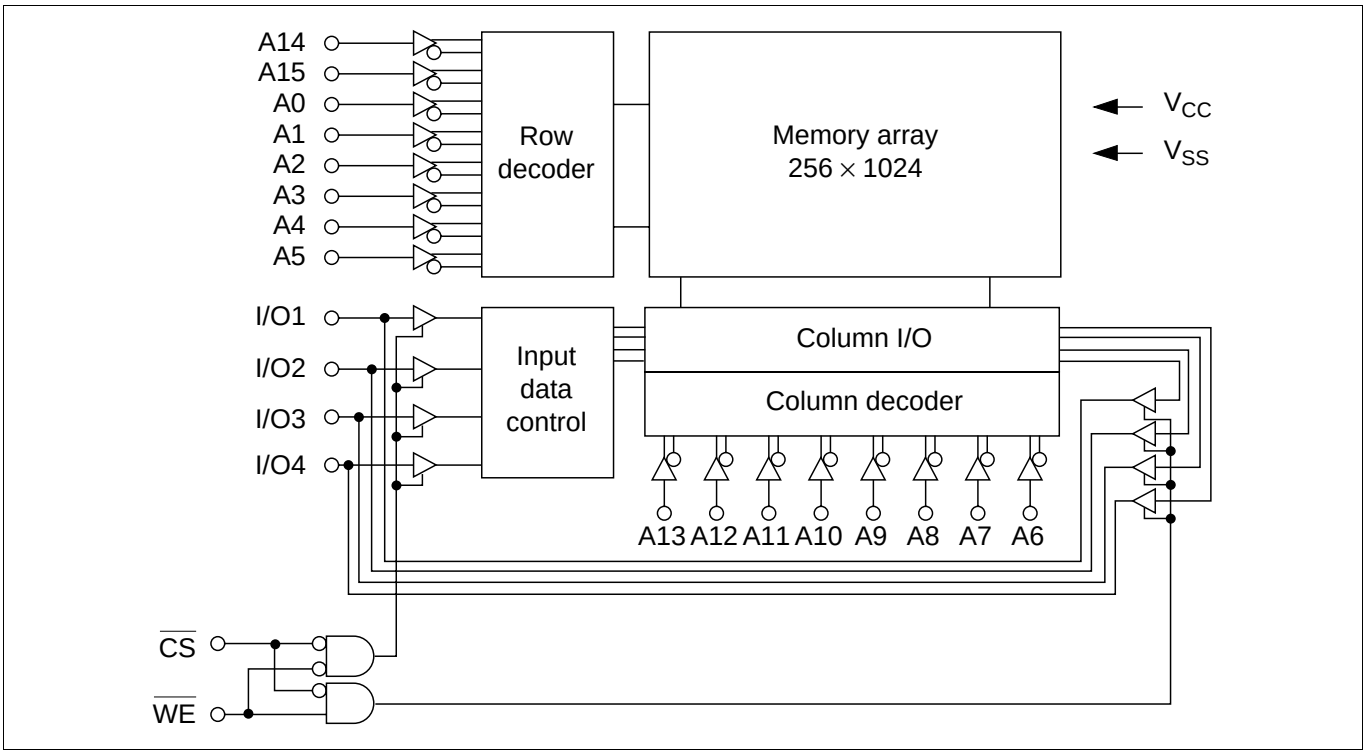


(Top view)

Pin Description

Pin Name	Function
A0–A15	Address
I/O1–I/O4	Input/output
$\overline{CS}$	Chip select
$\overline{WE}$	Write enable
V_{CC}	Power supply
V_{SS}	Ground

Block Diagram



Truth Table

$\overline{CS}$	$\overline{WE}$	Mode	V_{cc} Current	I/O Pin	Ref. Cycle
H	×	Not selected	I_{SB}, I_{SB1}	High-Z	—
L	H	Read	I_{CC}	Dout	Read cycle
L	L	Write	I_{CC}	Din	Write cycle

Note: ×: Don't care.

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Voltage on any pin relative to V_{SS}	Vin	–0.5[*1] to +7.0	V
Power dissipation	P_T	1.0	W
Operating temperature range	Topr	0 to +70	°C
Storage temperature range	Tstg	–55 to +125	°C
Storage temperature range under bias	Tbias	–10 to +85	°C

Note: 1. Vin min = –2.5 V for pulse widths ≤ 10 ns.

Recommended DC Operating Conditions (Ta = 0 to +70°C)

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	V_{CC}	4.5	5.0	5.5	V
	V_{SS}	0	0	0	V
Input high (logic 1) voltage	V_{IH}	2.2	—	6.0	V
Input low (logic 0) voltage	V_{IL}	–0.5[*1]	—	0.8	V

Note: 1. V_{IL} min = –2.0 V for pulse width ≤ 10 ns.

DC Characteristics (Ta = 0 to +70°C, V_{CC} = 5 V ± 10%, V_{SS} = 0 V)

		HM6208H-25			HM6208H-35/45				
Parameter	Symbol	Min	Typ[*2]	Max	Min	Typ[*2]	Max	Unit	Test Conditions
Input leakage current	I_{LI}	—	—	2.0	—	—	2.0	µA	V_{CC} = Max Vin = V_{SS} to V_{CC}
Output leakage current	I_{LO}	—	—	10.0	—	—	10.0	µA	$\overline{CS}$ = V_{IH}, V_{IO} = V_{SS} to V_{CC}
Operating power supply current	I_{CC}	—	60	120	—	50	100	mA	$\overline{CS}$ = V_{IL}, $I_{I/O}$ = 0 mA, min cycle, duty = 100%
	I_{CC1}	—	40	80	—	40	80	mA	$\overline{CS}$ = V_{IL}, $I_{I/O}$ = 0 mA, t cycle = 50 ns, duty = 100%
Standby power supply current	I_{SB}	—	20	40	—	15	30	mA	$\overline{CS}$ = V_{IH}, min cycle
Standby power supply current (1)	I_{SB1}	—	0.02	2.0	—	0.02	2.0		$\overline{CS}$ ≥ V_{CC} – 0.2 V, 0 V ≤ Vin < 0.2 V, or Vin ≥ V_{CC} – 0.2 V
	I_{SB1}[*1]	—	0.006	0.1[*1]	—	0.006	0.1[*1]		
Output low voltage	V_{OL}	—	—	0.4	—	—	0.4	V	I_{OL} = 8 mA
Output high voltage	V_{OH}	2.4	—	—	2.4	—	—	V	I_{OH} = –4.0 mA

Notes: 1. L-version
2. Typical values are at V_{CC} = 5.0 V, Ta = +25°C and not guaranteed.

Capacitance (Ta = 25°C, f = 1 MHz)[*1]

Parameter	Symbol	Min	Max	Unit	Test Conditions
Input capacitance	Cin	—	6	pF	Vin = 0 V
Input/output capacitance	$C_{I/O}$	—	11	pF	$V_{I/O}$ = 0 V

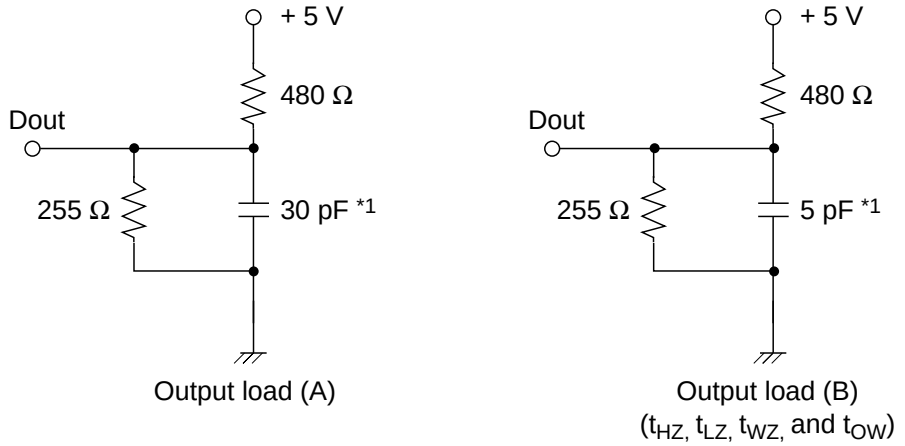
Note: 1. These parameters are sampled and not 100% tested.

AC Characteristics (Ta = 0 to +70°C, V_{CC} = 5 V ± 10%, unless otherwise noted)

Test Conditions

- Input pulse levels: V_{SS} to 3.0 V
- Input rise and fall time: 5 ns
- Input and output timing reference levels: 1.5 V
- Output load: See figure

Output Load



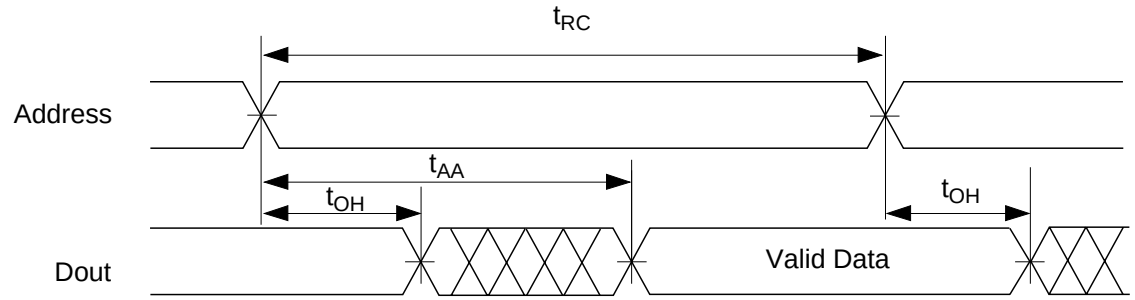
Note: 1. Including scope and jig

Read Cycle

		HM6208H-25		HM6208H-35		HM6208H-45		
Parameter	**Symbol**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	**Unit**
Read cycle time	t_{RC}	25	—	35	—	45	—	ns
Address access time	t_{AA}	—	25	—	35	—	45	ns
Chip select access time	t_{ACS}	—	25	—	35	—	45	ns
Output hold from address change	t_{OH}	5	—	5	—	5	—	ns
Chip selection to output in low-Z	t_{LZ} *1	5	—	5	—	5	—	ns
Chip deselection to output in high-Z	t_{HZ} *1	0	15	0	20	0	20	ns
Chip selection to power up time	t_{PU}	0	—	0	—	0	—	ns
Chip deselection to power down time	t_{PD}	—	15	—	25	—	30	ns

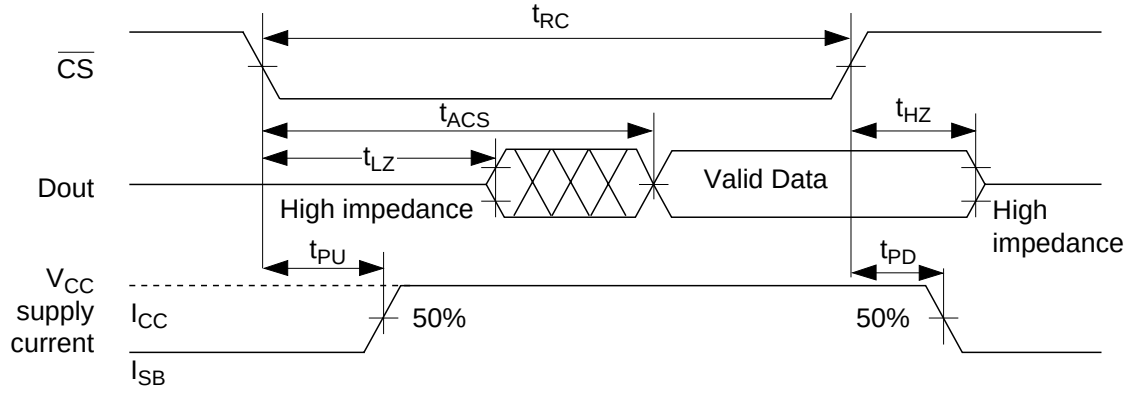
Note: 1. Transition is measured ±200 mV from steady state voltage with load (B). These parameters are sampled and not 100% tested.

Read Timing Waveform (1)



Notes: 1. $\overline{WE}$ is high for read cycle.
2. Device is continuously selected.

Read Timing Waveform (2)



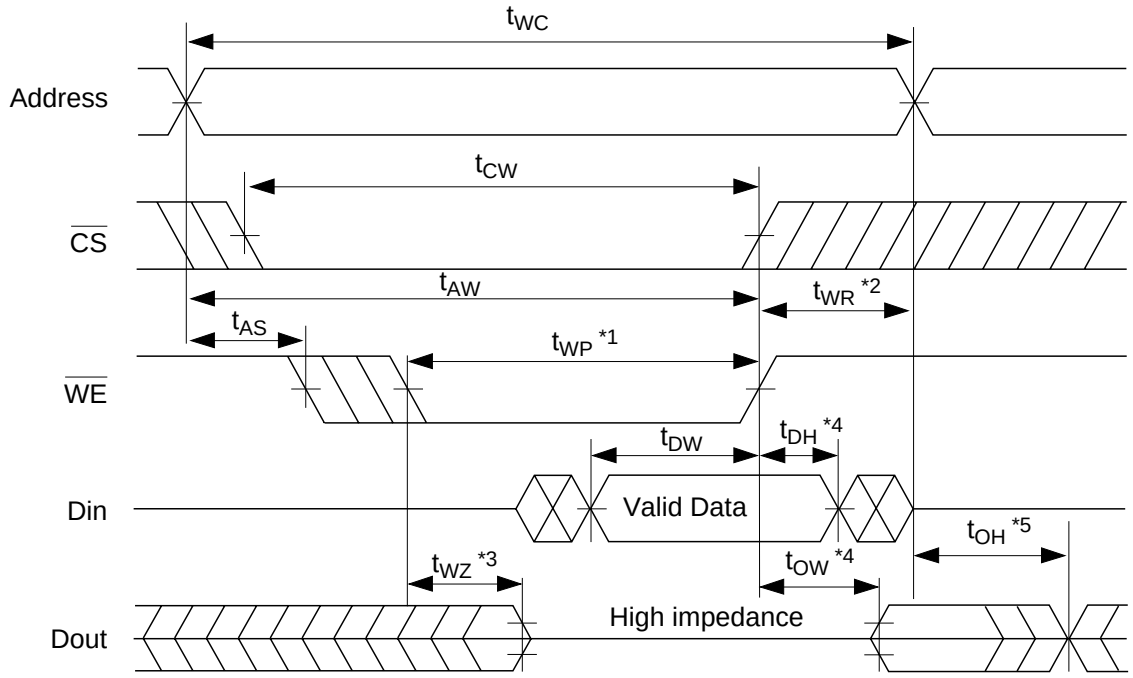
Notes: 1. $\overline{WE}$ is high for read cycle.
2. Address valid prior to or coincident with the $\overline{CS}$ transition to low.

Write Cycle

		HM6208H-25		HM6208H-35		HM6208H-45		
Parameter	**Symbol**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	**Unit**
Write cycle time	t_{WC}	25	—	35	—	45	—	ns
Chip selection to end of write	t_{CW}	20	—	30	—	40	—	ns
Address valid to end of write	t_{AW}	20	—	30	—	40	—	ns
Address setup time	t_{AS}	0	—	0	—	0	—	ns
Write pulse width	t_{WP}	20	—	25	—	30	—	ns
Write recovery time	t_{WR}	3	—	3	—	3	—	ns
Data valid to end of write	t_{DW}	15	—	20	—	20	—	ns
Data hold time	t_{DH}	0	—	0	—	0	—	ns
Write enabled to output in high-Z	t_{WZ}[*1]	0	8	0	10	0	15	ns
Output active from end of write	t_{OW}[*1]	0	—	0	—	0	—	ns

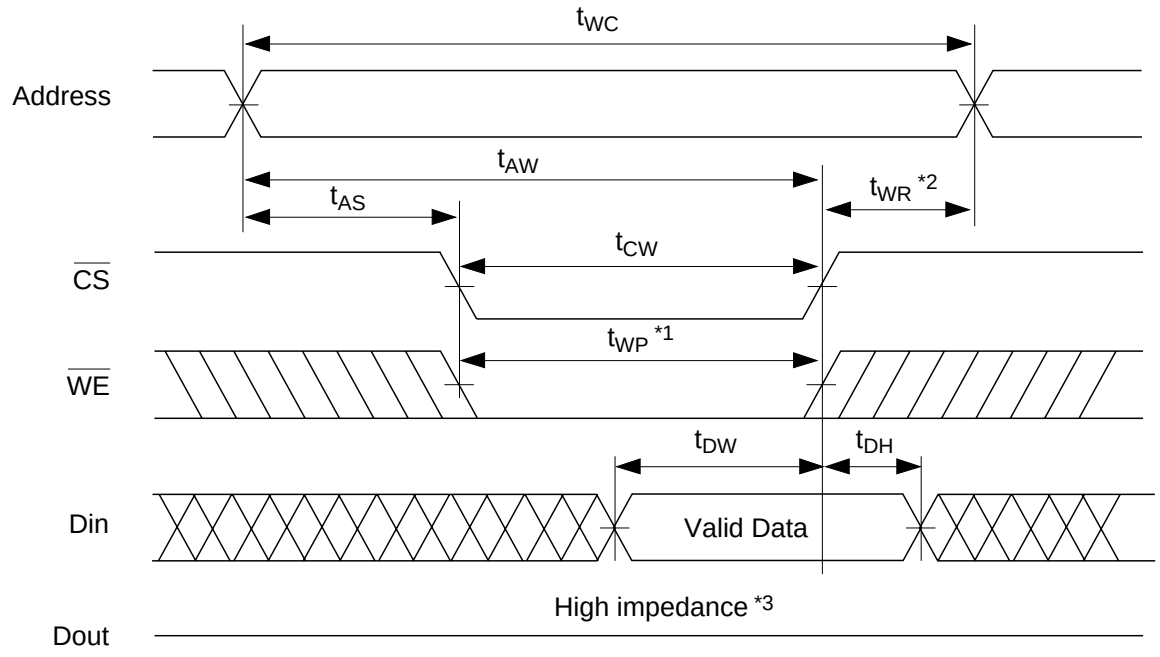
Note: 1. Transition is measured ±200 mV from high impedance voltage with load (B).
These parameters are sampled and not 100% tested.

Write Timing Waveform (1) ($\overline{WE}$ Controlled)



Notes: 1. A write occurs during the overlap of a low $\overline{CS}$ and a low $\overline{WE}$ (t_{WP}).
2. t_{WR} is measured from the earlier of $\overline{CS}$ or $\overline{WE}$ going high to the end of the write cycle.
3. During this period, I/O pins are in the output state. The input signals of the opposite phase to the outputs must not be applied.
4. If $\overline{CS}$ is low during this period, I/O pins are in the output state. The data input signals of opposite phase to the outputs must not be applied to them.
5. Dout is the same phase of write data of this write cycle.

Write Timing Waveform (2) ($\overline{CS}$ Controlled)



Notes: 1. A write occurs during the overlap of a low $\overline{CS}$ and a low $\overline{WE}$ (t_{WP}).
2. t_{WR} is measured from the earlier of $\overline{CS}$ or $\overline{WE}$ going high to the end of the write cycle.
3. If the $\overline{CS}$ low transition occurs simultaneously with the $\overline{WE}$ low transition or after the $\overline{WE}$ transition, the output buffers remain in a high-impedance state.

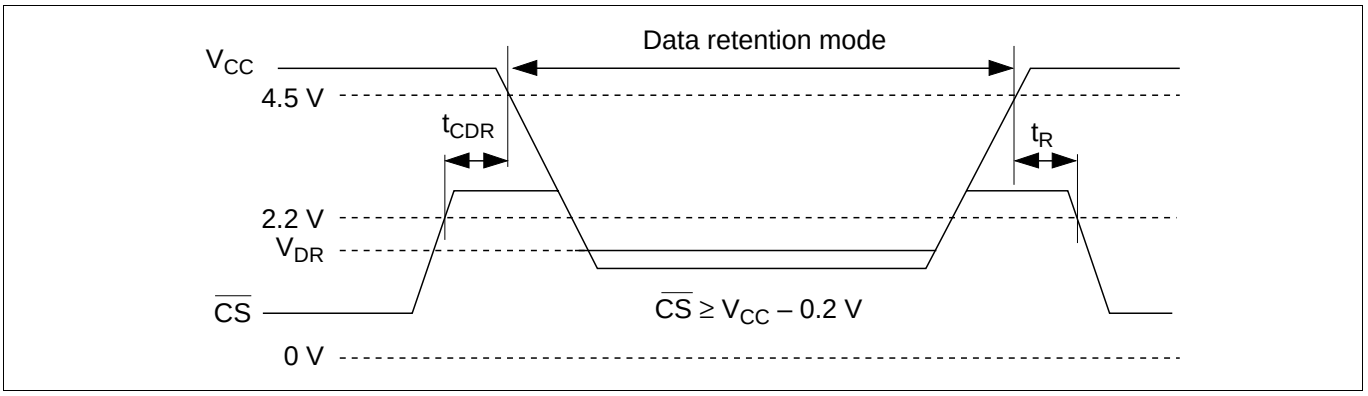
Low V_{CC} Data Retention Characteristics (Ta = 0 to +70°C)

These characteristics are guaranteed for the L-version only.

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
V_{CC} for data retention	V_{DR}	2.0	—	—	V	$\overline{CS} \geq V_{CC} - 0.2$ V, Vin ≥ V_{CC} – 0.2 V, or 0 V ≤ Vin < 0.2 V,or
Data retention current	I_{CCDR}	—	2	50*1	µA	
Chip deselect to data retention time	t_{CDR}	0	—	—	ns	
Operation recovery time	t_R	5	—	—	ms	

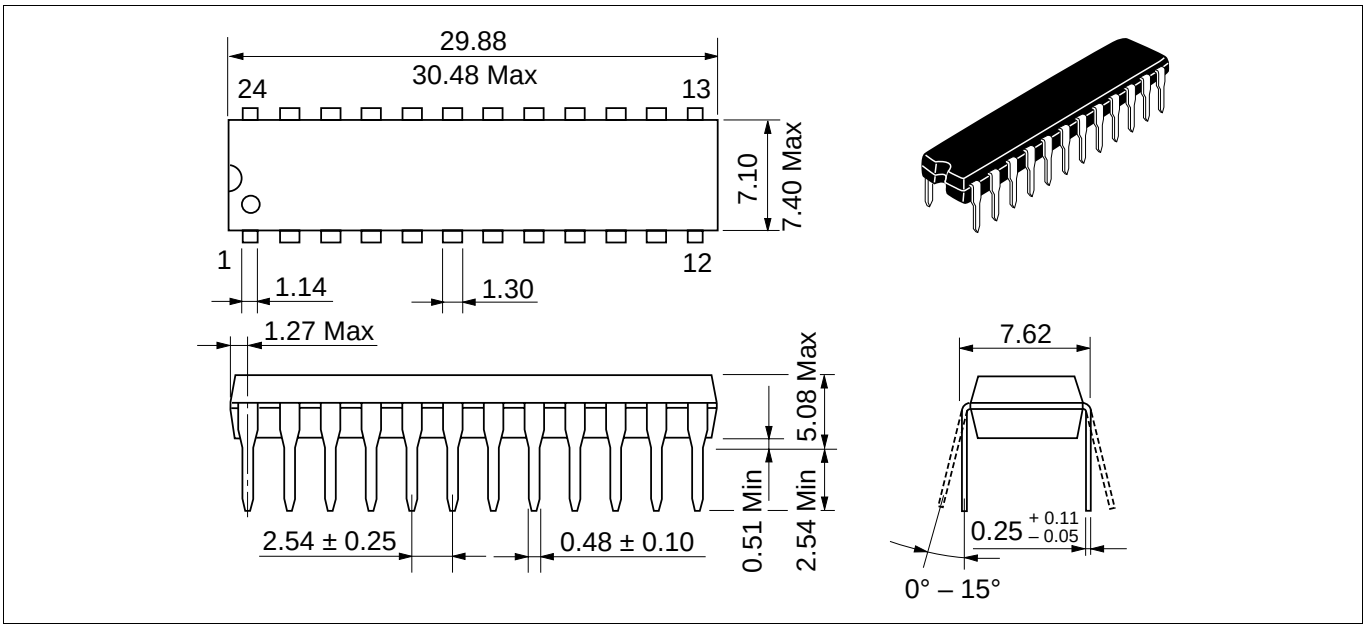
Note: 1. V_{CC} = 3.0 V

Low V_{CC} Data Retention Timing Waveform



Package Dimensions

HM6208HP/HLP Series (DP-24NC) Unit: mm



HM6208HJP/HLJP Series (CP-24D) Unit: mm